# Dual 1 W Output AMOLED Driver Supply

The NCP5810 is a dual—output DC/DC converter which can generate both a positive and a negative voltage. Both PWM converters achieve high efficiency for portable application. Thanks to the high output voltage accuracy and signal integrity the NCP5810 is particularly suitable for powering applications such as AMOLED display drivers. The output voltage of the inverter is fully configurable using external feedback resistors, where the output voltage of the boost is internally fixed. The switching regulator operates at 1.75 MHz which allows the use of small inductors and ceramic capacitors. In addition both converters are internally compensated which simplifies the design and reduces the PCB component count. Cycle—by—cycle peak current limit and thermal shut down provide value added features to protect the device. The NCP5810 is housed in a low profile space efficient 3 x 3 x 0.55 mm LLGA package.

#### **Features**

- High Overall Efficiency: 83% (Refer to Figure 4)
- Low Noise 1.75 MHz PWM DC/DC Converter
- Positive Output Fixed + 4.6 V
- Negative Output from − 2.0 to − 15.0 V
- High Output Voltage Accuracy
- Excellent Line Transient Rejection
- Soft Start to Limit Inrush Current
- Enable Control Facility with True-Shut Down
- Small LLGA 3 x 3 x 0.55 mm Package

#### **Typical Applications**

- AMOLED Driver Supply
  - Cellular Phones
  - MP3 Player
  - Digital Cameras
  - Personal Digital Assistant and Portable Media Player
  - ◆ GPS



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12 PIN LLGA MU SUFFIX CASE 513AD

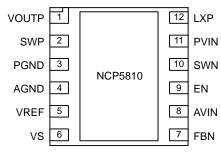
#### **MARKING DIAGRAM**



5810 = Device Code A = Assembly Location

Y = Year W = Work Week ■ = Pb-Free Package

(Note: Microdot may be in either location)

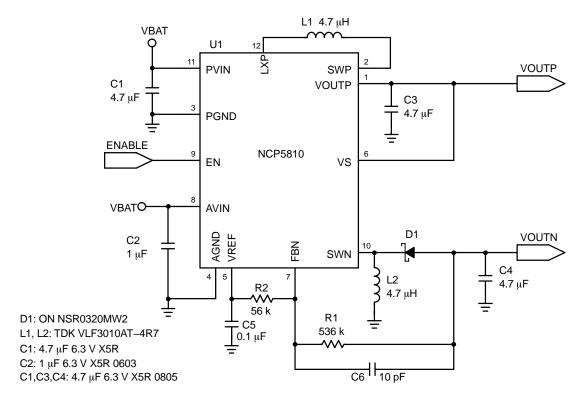


(Top View) 12-pin 3 x 3 x 0.55 mm LLGA

Exposed pad must be soldered to PCB Ground plane

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.



**Figure 1. Typical Application Circuit** 

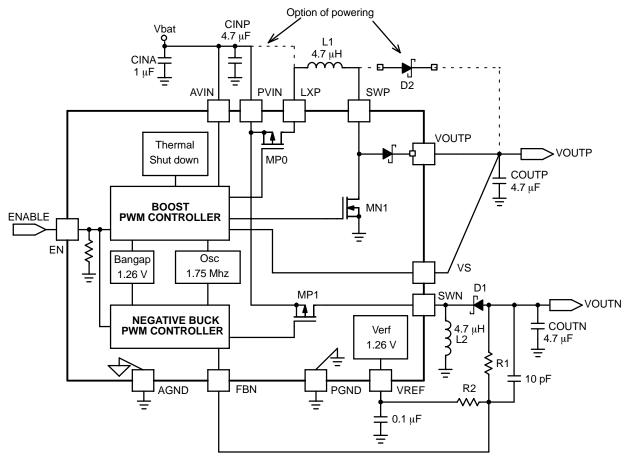


Figure 2. Simplified Block Diagram

#### PIN FUNCTION DESCRIPTION

Pin	Pin Name	Туре	Description		
1	VOUTP	OUTPUT	<b>Positive Power Output:</b> A filter capacitor is necessary on this pin for the stability of the loop, to smooth the current flowing into the load, and limit the noise created by the fast transients present i this circuitry. A 4.7 $\mu$ F ceramic bypass capacitor to GND is recommended. Cares must be observed to avoid EMI through the PCB copper tracks connected to this pin.		
2	SWP	POWER	Switch LXP: Positive power switch pin where one end of the L1 inductor is connected. Typical application uses a 4.7 μH inductor.		
3	PGND	POWER	<b>Power Ground:</b> This pin is the power ground and carries the high switching current. A high quality ground must be provided to avoid any noise spikes/uncontrolled operation. Cares must be observed to avoid high-density current flow in a limited PCB copper track.		
4	AGND	POWER	Analog Ground: This pin is the analog ground of the device notably used by VREF.		
5	VREF	OUTPUT	<b>Voltage Reference:</b> This output provides a 1.265 V voltage reference used notably for the negative feedback resistive network.		
6	VS	INPUT	Positive Output Voltage Sense: This pin is the output voltage sense input for the positive boost converter and must be connected to COUTP bypass capacitor.		
7	FBN	INPUT	<b>Feedback Negative:</b> This pin is the feedback voltage input for the negative Buck–Boost inverter. The middle point of a resistive bridge divider must be connected here. The resistive network must be connected between VREF and the anode of external Schottky.		
8	AVIN	POWER	Analog Power Supply: The external voltage supply is connected to this pin. A 4.7 $\mu$ F ceramic capacitor must be connected across this pin and the power ground to achieve the specified output power parameters.		
9	EN	INPUT	<b>Enable:</b> An active high logic level on this pin enables the circuit. A built–in pull–down resistor disa the device if the pin is left open. Also in disable condition the device provide a true cut–off from PV to VOUTP and SWN.		
10	SWN	INPUT	Switch Negative: Negative power switch pin where one end of the L2 inductor is connected. Typic application uses a $4.7~\mu\text{H}$ inductor.		
11	PVIN	POWER	<b>Power Supply:</b> This pin is the power supply of the device. A $4.7~\mu F$ ceramic capacitor or larger must bypass this input to the ground. This capacitor should be placed as close a possible to this input.		
12	LXP	POWER	<b>Switch LXP:</b> The inductor should be connected between this node and SWP. This output supplies power from PVIN and give a true–cut off function in disable condition.		

#### **MAXIMUM RATINGS** (Note 1)

Rating	Symbol	Value	Unit
Power Supply Voltage (Note 2)	V <sub>bat</sub>	7.0	V
Human Body Model (HBM) ESD Rating are (Note 3)	ESD HBM	2000	V
Machine Model (MM) ESD Rating are (Note 3)	ESD MM	200	V
Digital Input Voltage Digital Input Current	ENP, ENN	$-0.3 \le V_{in} \le V_{bat} + 0.3$	V mA
LLGA 3x3 mm package (Notes 6 and 7) Thermal Resistance Junction–to–Case	$R_{ heta JC}$	12	°C/W
Operating Ambient Temperature Range	T <sub>A</sub>	-40 to +85	°C
Operating Junction Temperature Range	TJ	-40 to +125	°C
Maximum Junction Temperature	T <sub>JMAX</sub>	+150	°C
Storage Temperature Range	T <sub>STG</sub>	-65 to +150	°C
Moisture Sensitivity (Note 5)	MSL	Level 1	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. Maximum electrical ratings are defined as those values beyond which damage to the device may occur at  $T_A = 25^{\circ}\mathrm{C}$
- 2. According to JEDEC standard JESD22-A108B.
- 3. This device series contains ESD protection and passes the following tests: Human Body Model (HBM) ±2.0 kV per JEDEC standard: JESD22-A114 for all pins. Machine Model (MM) ±200 V per JEDEC standard: JESD22-A115 for all pins.
- Latchup Current Maximum Rating: ±100 mA per JEDEC standard: JESD78., class II
   Moisture Sensitivity Level (MSL): 1 per IPC/JEDEC standard: J-STD-020A.

- The thermal shutdown set to 165°C (typical) avoids irreversible damage on the device due to power dissipation.
   The R<sub>0CA</sub> is dependent on the PCB heat dissipation. The maximum power dissipation (P<sub>D</sub>) is dependent on the min input voltage, the max output

current and external components selected.
$$R_{\theta CA} = \frac{125 - T_A}{P_D} - R_{\theta JC}$$

**ELECTRICAL CHARACTERISTICS** Min & Max Limits apply for  $T_A$  between  $-40^{\circ}C$  to  $+85^{\circ}C$  and  $V_{IN}$  between 2.7 V to 4.6 V (Unless otherwise noted). Typical values are referenced to  $T_A = +25^{\circ}C$  and  $V_{IN} = 3.7$  V (Unless otherwise noted)

Symbol	Min	Тур	Max	Unit
V <sub>OUTP</sub>	4.55	4.6	4.65	V
I <sub>PEAKP_MAX</sub>	530	700	800	mA
P0 <sub>MOS</sub> R <sub>DSON</sub>	-	320	640	mΩ
N <sub>1MOS</sub> R <sub>DSON</sub>	-	300	600	mΩ
N <sub>1MOS</sub> L	-	0.05	0.5	μА
E <sub>FF</sub>	-	85	-	%
I <sub>OUTP</sub>	0	270 –	- 145	mA
L <sub>INE_RP</sub>	-	_	10	mV
L <sub>INE_TP</sub>	_	4	_	mV
P <sub>SRRP</sub>	_ _	60 40		dB
L <sub>OAD RP</sub>	_	_	0.5	%/100mA
L <sub>TRP</sub>	-	_	100	mV
-	J	!	!	<del>. !</del>
V <sub>OUTN</sub>	-15	_	-2.0	V
I <sub>PEAKN_MAX</sub>	620	800	920	mA
P <sub>2MOS</sub> R <sub>DSON</sub>	_	700	1400	mΩ
P <sub>2MOS</sub> L	_	0.05	0.5	μА
E <sub>FF</sub>	-	80	-	%
P <sub>OUTN</sub>	_ 0	175 -	- 100	mA
O <sub>VR</sub>	-1 %	1.265	+1 %	V
F <sub>BVN</sub>	-2 %	0.632	+2 %	mV
F <sub>BICN</sub>	-50	-	50	nA
L <sub>INE_RN</sub>	_	_	20	mV
L <sub>INE_TN</sub>	-	4	_	mV
P <sub>SRRN</sub>	- -	60 40		dB
L <sub>OAD RN</sub>	_	_	0.5	%/100mA
OAD KIV	4			
	Symbol  Voutp  IPEAKP_MAX  POMOS RDSON  N1MOS RDSON  N1MOS L  EFF  IOUTP  LINE_RP  LINE_TP  PSRRP  LOAD_RP  LTRP  VOUTN  IPEAKN_MAX  P2MOS RDSON  P2MOS L  EFF  POUTN  OVR  FBVN  FBICN  LINE_TN  PSRRN	Symbol   Min	VOUTP         4.55         4.6           IPEAKP_MAX         530         700           POMOS RDSON         -         320           N1MOS RDSON         -         300           N1MOS L         -         0.05           EFF         -         85           IOUTP         0         270           0         -         -           LINE_RP         -         -           LINE_TP         -         4           PSRRP         -         60           -         40         -           LOAD_RP         -         -           LTRP         -         -           VOUTN         -15         -           IPEAKN_MAX         620         800           P2MOS RDSON         -         700           P2MOS RDSON         -         700           P2MOS L         -         0.05           EFF         -         80           POUTN         -         175           0         -         175           0         -         1265           FBVN         -         2%         0.632           FBICN	Symbol   Min   Typ   Max

ELECTRICAL CHARACTERISTICS (Min & Max Limits apply for T<sub>A</sub> between -40°C to +85°C and V<sub>IN</sub> between 2.7 V to 4.6 V. Typical values are referenced to  $T_A = +25^{\circ}C$  and  $V_{IN} = 3.7$  V, unless otherwise noted)

Rating	Symbol	Min	Тур	Max	Unit
Operational Power Supply	V <sub>IN</sub>	2.7	-	4.6	V
Internal Oscillator Frequency, T <sub>A</sub> = 25°C, V <sub>IN</sub> = 3.7 V	Fosc	1.6	1.75	1.9	MHz
Maximum Duty Cycle	M <sub>DCY</sub>	87	90	_	%
Stand by Current at $I_{OUTP} = I_{OUTN} = 0$ mA, EN = Low $V_{IN} = 4.2$ V, $T_A$ between 0 to +85°C	I <sub>STB</sub>	-	_	2.0	μА
Quiescent Current @ V <sub>OUTN</sub> = -5.4 V @ T <sub>A</sub> = +25°C Switching (Note 9) No Switching	IQ	- -	1.5 1.0	3.0	mA
Soft Start Time to limit the Inrush Current	S <sub>ST</sub>	_	1.0	_	ms
Thermal Shut Down Protection	T <sub>SD</sub>	_	165	-	°C
Thermal Shut Down Protection Hysteresis	T <sub>SDH</sub>	_	15	_	°C
Voltage Input Logic Low	V <sub>IL</sub>	_	-	0.4	V
Voltage Input Logics High	V <sub>IH</sub>	1.2	-	-	V
EN pin Pull Down Resistance	R <sub>ENP</sub>	280	400	670	kΩ

#### NOTES:

- 8. Efficiency is defined by 100 \* (Pout / Pin), Vin = 3.1 to 4.2 V, L = VLF3010AT-4R7MR70 (DCR = 280 m $\Omega$  max, Isat = 700 mA), Load = 15 to 30 mA, Voutn = -5.4 V.
- 9. Guaranteed by design and characterized.
- 10. Typical application circuit and components depicted Figure 1.
- 11. Tested at 25°C and guaranteed from -40°C to +85°C by characterization. 12. Line drop and rise between 3.4 to 2.9 V in 50  $\mu$ s at  $I_{OUT} = 25$  mA,  $V_{OUTN} = -5.4$  V. 13. Ripple = 0.2 V p-p at 25°C, Cout = 4.7  $\mu$ F,  $I_{OUT} = 0$  to 100 mA,  $V_{IN} = 3.7$  V. 14.  $I_{OUT}$  from 0 to 100 mA.

- 15. Load step 10 to 90 mA and 90 to 10 mA, rising and falling edge in 10  $\mu$ s, Cout = 4.7  $\mu$ F, V<sub>IN</sub> = 3.7 V.

#### TYPICAL OPERATING CHARACTERISTICS

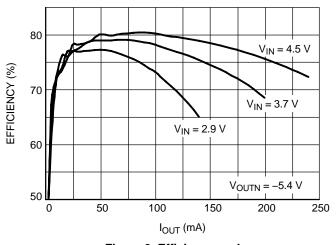


Figure 3. Efficiency vs. I<sub>OUT</sub> L = MURAWA CXFU0208-4R7

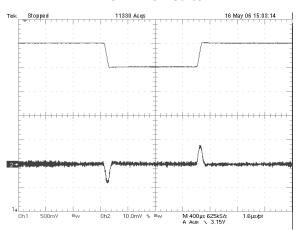


Figure 5. Line Transient Response  $V_{OUTP}$  at 100 mA 1 VBAT, 500 mV/div DC, from 3.5 to 3.0 V in 50  $\mu$ s 2 VOUTP, 10 mV/div AC, T = 400  $\mu$ s/div

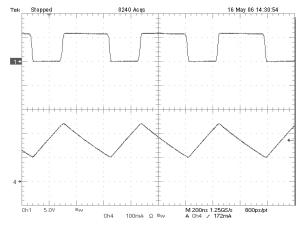
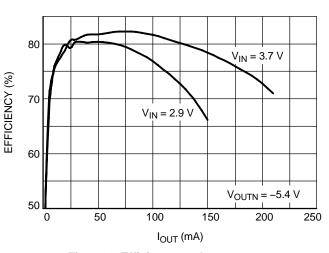


Figure 7. Continuous Conduction Mode (CCM)
1 SWP, 5 V/div DC, 4 I<sub>LP</sub>, 100 mA/div, DC, I<sub>OUTP</sub> = 100 mA



**Figure 4. Efficiency vs. I<sub>OUT</sub>**, L = MURAWA CXFU0208–4R7 plus Optional D2 NSR0320MW2

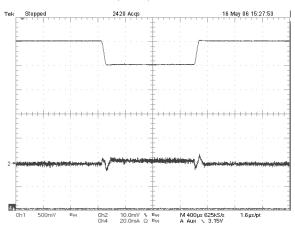


Figure 6. Line Transient Response  $V_{OUTN}$  = -5.4 V, 100 mA 1 VBAT, 500 mV/div DC, from 3.5 to 3.0 V in 50  $\mu$ s 2 VOUTN, 10 mV/div AC, T = 400  $\mu$ s/div

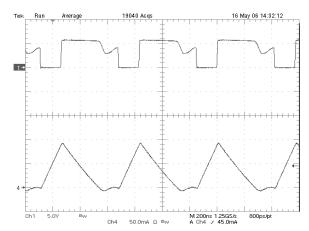


Figure 8. Discontinuous Current Mode (DCM) 1 SWP, 5 V/div, DC 4  $I_{LP}$ , 50 mA/div, DC,  $I_{OUTP}$  = 20 mA

Figures 7 and 8 have been done at VBAT = 3.7 V,  $V_{OUTN} = -5.4 \text{ V}$ 

#### TYPICAL OPERATING CHARACTERISTICS

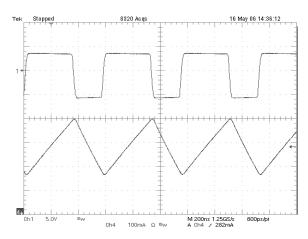


Figure 9. Continuous Conduction Mode (CCM)
1 SWN, 5 V/div DC, 4 I<sub>LN</sub>, 100 mA/div, DC, I<sub>OUTN</sub> = 100 mA

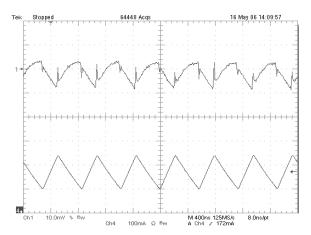
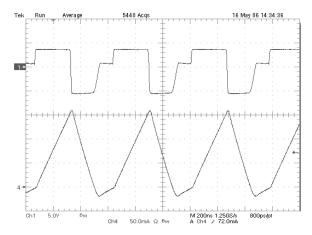


Figure 11. Positive Output Voltage Ripple in CCM 1 V<sub>OUTP</sub>, 10 mV/div AC, 4 I<sub>LP</sub>, 100 mA/div DC, I<sub>OUTP</sub> = 100 mA



**Figure 10. Discontinuous Current Mode (DCM)** 1 SWN, 5 V/div, DC 4 I<sub>LN</sub>, 50 mA/div, DC, I<sub>OUTN</sub> = 20 mA

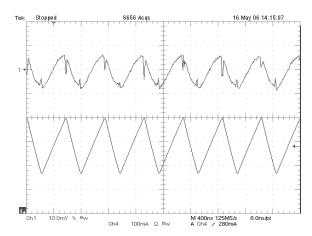


Figure 12. Negative Output Voltage Ripple in CCM 1  $V_{OUTN}$ , 10 mV/div AC, 4  $I_{LN}$ , 100 mA/div DC,  $I_{OUTN}$  = 100 mA

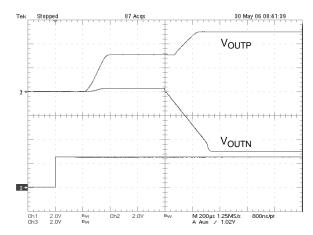


Figure 13. Start-Up After Enable
1 VOUTP, 2 V/div, 2 VOUTN, 2 V/div, 3 EN pin, 2 V/div

Figures 9 through 12 have been done at VBAT = 3.7 V and schematic depict Figure 1

#### **DETAILED OPERATING DESCRIPTION**

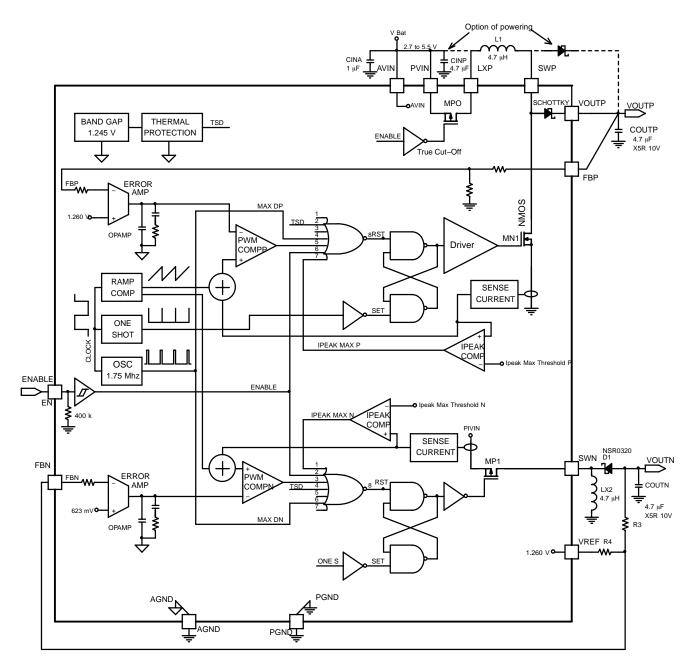


Figure 14. Functional Block Diagram

#### **Detailed Descriptions**

The NCP5810 is a dual—output DC/DC converter which can generate both a positive and a negative voltage. The output voltage of the inverter is fully configurable using external feedback resistors. The switching regulator operates at 1.75 MHz which allows the use of small inductors and ceramic capacitors. The both converters are internally compensated which simplifies the design and reduces the PCB component count. Cycle—by—cycle peak current limit and thermal provide value added features to protect the device.

#### **Boost Operation**

The internal oscillator provides a 1.75 MHz clock signal to trigger the PWM controller on each rising edge (SET signal) which starts a cycle. During this phase the low side MN1 switch is turned on thus increasing the current through the inductor L1. The switch current is measured by the SENSE CURRENT and added to the RAMP COMP signal. Then PWM COMPP compares the output of the adder and the signal from ERROR AMP. When the comparator threshold is exceeded, the MN1 power switch is turned off until the rising edge of the next clock cycle. In

addition, there are five functions which can reset the flip-flop logic to switch off the MN1. The MAX DP monitors the pulse width and if it exceeds 88% (nom) of the cycle time the switch will be turned off. This limits the switch from being on for more than one cycle. IPEAK COMP compares the sensed inductor current with the IPEAK\_MAX threshold set at 700 mA (nom). If the current exceeds this value, the controller turns off the NMOS switch for the remainder of the cycle. This is a safety function to prevent any excessive current that could overload the inductor and the power stage. The boost regulator is internally compensated and provides a minimum of 45° phase margin.

#### **Buck-Boost Inverter Operation**

Figure 9 depicts the two intervals of the buck-boost operation in Continuous Conduction Mode (CCM) in a simplified way. During the first interval, the internal PMOS power switch is turned on and the external Schottky diode is reverse biased. The inductor stores energy through the battery while the load is supplied by the output capacitor to maintain regulation. During the second interval, the switch is turned off and the diode is forward biased, this allows the energy stored in the inductor to be supplied to both the load and the capacitor.

In CCM, the voltage ratio of a buck-boost inverter converter can be expressed as:

$$\frac{V_{OUT\_N}}{V_{IN}} = \frac{D}{1-D} \text{ where } D = \frac{T_{ON}}{T_{SW}}$$

The internal oscillator provides a 1.75 MHz clock signal to trigger the PWM controller on each rising edge (SET signal) which starts a cycle. During this phase the high side PMOS switch is turned on thus increasing the current through the inductor. The switch current is measured by the SENSE CURRENT and added to the RAMP COMP signal. Then PWM COMPN compares the output of the adder and the signal from ERROR AMP. When the comparator threshold is exceeded, the PMOS power switch is turned off until the rising edge of the next clock cycle. In addition, there are five functions which can reset the flip-flop logic to switch off the NMOS. The MAX DUTY CYCLE COMP monitors the pulse width and if it exceeds 88% (nom) of the cycle time the switch will be turned off. This limits the switch from being on for more than one cycle. IPEAK COMP compares the sensed inductor current with the IPEAK\_MAX threshold set at 800 mA (nom). If the current exceeds this value, the controller turns off the PMOS switch for the remainder of the cycle. This is a safety function to prevent any excessive current that could overload the inductor and the power stage. The buck-boost inverter is internally compensated and provides a minimum of 45° phase margin.

#### Sequencing

The sequencing is designed internally. The positive output first comes up, and then the negative output does.

#### **High Output Voltage Accuracy**

NCP5810 integrates a very accurate internal voltage reference (1% nom). Combined with the use of precision feedback resistors, the NCP5810 will achieve highly precise output voltages.

## Excellent Line Transient Rejection and High Power Supply Rejection Ratio

High output voltage accuracy and signal integrity makes the NCP5810 the perfect solution for biasing Active Matrix OLED displays. In order to have a steady, clean display, OLEDs have to be biased by a very accurate voltage with high immunity to line and load transients. Both regulators have been specifically designed with high loop gain and high phase margin to satisfy the great constraints of AMOLED driving.

The boost converter features a high power supply rejection ratio of 60 dB (nom).

PSRR is defined by

$$-\ 20 LOG \left( \frac{OutputRipple}{VinRipple} \right)$$

#### **Enable**

This input logic allows enabling and disabling the converter. An active high logic level on this pin enables the device. A built—in pull—down resistor disables the device if the pin is left open.

#### **True Shut Down**

When in disable condition, the switch MP0 is turned off and truly isolates the battery from the output. The True shut down eliminates the leakage current from the battery to the load and significantly reduces battery consumption during disable condition, thus increasing battery life.

#### **Inrush Current Limiting Circuitry**

Before the NCP5810 boost converter is turned on, it is unknown whether the output capacitor COUTP is charged or discharged. If the output capacitor is discharged, a common boost converter shows high inductor inrush current at start—up. The internal circuitry of the NCP5810 has been carefully designed to limit the amplitude of the inrush current at start—up.

#### **Thermal Shutdown**

When the IC junction temperature exceeds 165°C (nom), the power section of the device is disabled. Normal operation will resume when the junction temperature drops below 150°C (nom).

#### Design Procedure

#### **Buck-Boost Inverter Output Voltage Setting**

The output voltage of the buck-boost inverter is also adjusted using external feedback resistors, and can be set from -2 V down to -15 V. Unlike for the boost converter, the lower feedback resistor R2 does not use the ground as a reference but uses the reference voltage (nom 1.265 V).

R2 is placed between the feedback pin FBN (nom 632 mV) and the reference pin REF. As for the boost converter, the current flowing out of the feedback resistors must be as low as possible to ensure high efficiency in low load conditions. Nevertheless the feedback resistor impedance must not be too high to keep good voltage accuracy. Therefore it is recommended to use values in the 10 k $\Omega$  to 100 k $\Omega$  range for the lower resistor R2. The upper feedback resistor R1 can calculated using the following equation:

$$R_{1} = R_{2} \times \left(\frac{V_{OUTN} - V_{FBN}}{V_{FBN} - V_{REF}}\right)$$

$$But: V_{FBN} = \frac{V_{REF}}{2}$$

So: 
$$R_1 = R_2 \times \left(1 + \frac{2 \times |V_{OUTN}|}{V_{REF}}\right)$$

For example, should one need -5.4 V for  $V_{OUTN}$ , if a  $56 \, k\Omega \, \pm 1\%$  is selected of R2, R1 should be selected according to the following equation:

$$R_1 = 56 \times \left(1 + \frac{2 \times 5.4}{1.265}\right) = 536 \text{ k}\Omega \pm 1\%$$

#### **Inductor Selection**

Three different electrical parameters need to be considered when selecting an inductor, the absolute value of the inductor, the saturation current and the DCR. During normal operation, the NCP5810 is intended to operate in Continuous Conduction Mode (CCM). The two equations below can be used to calculate the peak current for each converters:

$$I_{PEAK\_P} = \frac{I_{OUT\_P}}{\eta_P \times (1 - D_P)} + \frac{V_{IN} \times D_P}{2 \times L_P \times F}$$

For the boost converter

$$I_{PEAK\_N} = \frac{I_{OUT\_N} \times D_N}{\eta_N \times (1 - D_N)} + \frac{V_{IN} \times D_N}{2 \times L_N \times F}$$

For the buck-boost inverter

Where  $V_{IN}$  is the battery voltage,  $I_{OUT\_X}$  is the load current, L the inductor value, F the switching frequency, and  $D_X$  the duty cycle.

The global converter efficiency  $\eta$  varies with load current. A good approximation is to use  $\eta=0.8$  from the boost and  $\eta=0.75$  for the buck-boost inverter. It is important to ensure that the inductor current rating is high enough such that it not saturate. As the inductor size is reduced, the peak current for a given set of conditions increases along with higher current ripple so it is not possible to deliver maximum output power at lower inductor values. Finally an acceptable DCR must be selected regarding losses in the coil and must be lower than  $300~\text{m}\Omega$  to limit excessive voltage drop. In addition, as DCR is reduced, overall efficiency will improve. The inductor value should range between  $2.7~\mu\text{H}$  and  $6.8~\mu\text{H}$ ,

typically for each DC/DC converter, it is recommended to use a  $4.7~\mu H$  low profile inductor. Some recommended inductors include but are not limited to:

TDK: VLF3010AT-4R7MR70 (1.0 mm)

TDK: MLP3216S2R7T (0.6 mm) SUMIDA: CDH2D09BNP (1.0 mm) MURAWA CXFU0208–4R7 (0.8 mm)

#### **Schottky Diode Selection**

An external diode is required for the rectification of the negative output. The reverse voltage rating of the selected diode must be equal to or greater than the difference between the output voltage of the inverter and the input voltage. The average current rating of the diode must be greater than the maximum output load current. The peak current rating must be larger than the maximum peak inductor current. It is recommended to use a Schottky diode with lower forward voltage to minimize the power dissipation and therefore to maximize the efficiency of the converter

Also a particular care must be observed for parasitic capacitance versus reverse voltage and leakage current versus junction diode temperature. Both parameters are impacting the efficiency in low load condition and switching quiescent current.

Some recommended Schottky diodes include but are not limited to:

ON SEMICONDUCTOR: NSR0320MW2 ON SEMICONDUCTOR: RB521S30

ROHM: RSX051VA-30 PHILIPS: PMEG2005AEL

#### **Input and Output Capacitors**

 $C_{OUTP}$  and  $C_{OUTN}$  store energy during the  $T_{OFF}$  phase and sustain the load during the  $T_{ON}$  phase. In order to minimize the output ripple, a 4.7  $\mu F$  low ESR multi-layer ceramic capacitor type X5R is recommended. To achieve high performances (signal integrity) two 4.7  $\mu F$  6.3 V X5R should be used to bypass the input supply,  $C_{INP}$  and  $C_{INA}$ .

Also a particular care must be observed for DC-bias effects in ceramic capacitor. Actually smaller the case-size and higher the DC bias voltage, the bigger drop in capacitance. For a stability viewpoint the percentage drop in capacitance for the chosen input or output operating voltage must be limit to 20%.

Some recommended capacitors include but are not limited to:

4.7 μF 6.3 V 0603

TDK: C1608X5R0J475MT

TDK: CGB4B1X5R0J475M (0.5 mm)

4.7 μF 10 V 0805

TDK: C2012X5R1A475MT MURATA: GRM219R61A475KE

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NCP5810MUTXG	LLGA-123x3 mm (Pb-Free)	3000 / Tape & Reel

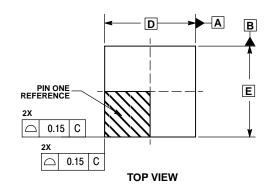
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

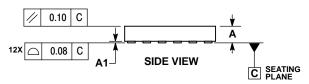
#### Demo Board Available:

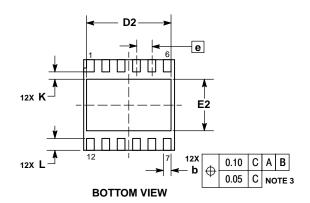
• The NCP5810GEVB/D evaluation board that configures the device in typical application to supply constant voltage.

#### PACKAGE DIMENSIONS

#### 12 PIN LLGA **MU SUFFIX** CASE 513AD **ISSUE A**







#### NOTES:

- NOTES.

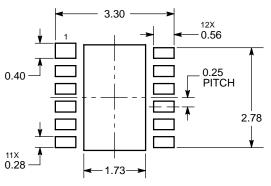
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. DIMENSION 6 APPLIES TO PLATED
- TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM TERMINAL TIP.
- COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.50	0.60		
A1	0.00	0.05		
b	0.20	0.30		
D	3.00 BSC			
D2	2.75	2.85		
E	3.00 BSC			
E2	1.65	1.75		
е	0.50 BSC			
K	0.20			
L	0.35	0.45		

#### SOLDERING FOOTPRINT\*



**DIMENSIONS: MILLIMETERS** 

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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